# 74AVC8T245

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Rev. 3 — 28 September 2011

Product data sheet

# 1. General description

The 74AVC8T245 is an 8-bit, dual supply transceiver that enables bidirectional level translation. It features two 8-bit input-output ports (An and Bn), a direction control input (DIR), a output enable input ( $\overline{\text{OE}}$ ) and dual supply pins ( $V_{CC(A)}$  and  $V_{CC(B)}$ ). Both  $V_{CC(A)}$  and  $V_{CC(B)}$  can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins An,  $\overline{\text{OE}}$  and DIR are referenced to  $V_{CC(A)}$  and pins Bn are referenced to  $V_{CC(B)}$ . A HIGH on DIR allows transmission from An to Bn and a LOW on DIR allows transmission from Bn to An. The output enable input ( $\overline{\text{OE}}$ ) can be used to disable the outputs so the buses are effectively isolated.

The device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either  $V_{CC(A)}$  or  $V_{CC(B)}$  are at GND level, both An and Bn are in the high-impedance OFF-state.

### 2. Features and benefits

- Wide supply voltage range:
  - ◆ V<sub>CC(A)</sub>: 0.8 V to 3.6 V
  - V<sub>CC(B)</sub>: 0.8 V to 3.6 V
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114E Class 3B exceeds 8000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101C exceeds 1000 V
- Maximum data rates:
  - 380 Mbit/s (≥ 1.8 V to 3.3 V translation)
  - 260 Mbit/s (≥ 1.1 V to 3.3 V translation)
  - 260 Mbit/s (≥ 1.1 V to 2.5 V translation)
  - 210 Mbit/s (≥ 1.1 V to 1.8 V translation)
  - 150 Mbit/s (≥ 1.1 V to 1.5 V translation)
  - 100 Mbit/s (≥ 1.1 V to 1.2 V translation)



## 8-bit dual supply translating transceiver; 3-state

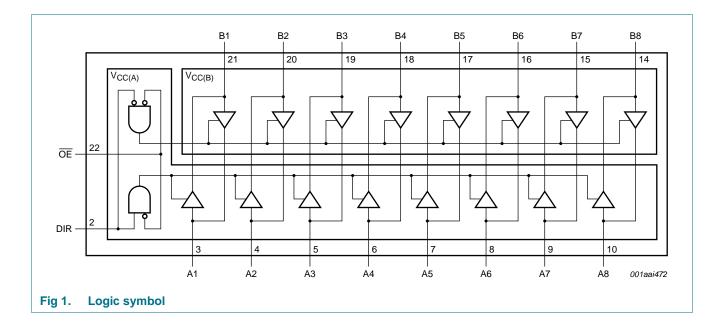
- Suspend mode
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

# 3. Ordering information

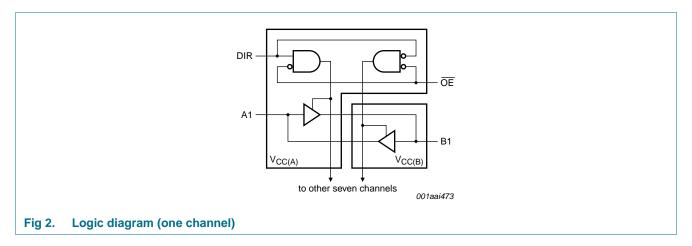
Table 1. Ordering information

Type number	Package				
	Temperature range Name Description				
74AVC8T245PW	–40 °C to +125 °C	TSSOP24	plastic thin shrink small outline package; 24 leads; body width 4.4 mm	SOT355-1	
74AVC8T245BQ	–40 °C to +125 °C	DHVQFN24	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body $3.5\times5.5\times0.85$ mm	SOT815-1	

# 4. Functional diagram

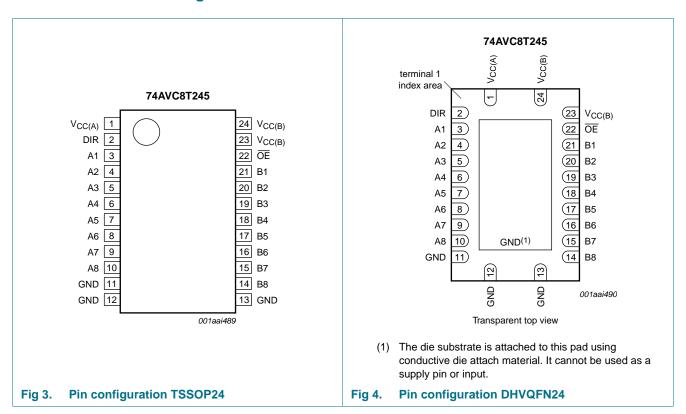


### 8-bit dual supply translating transceiver; 3-state



# 5. Pinning information

## 5.1 Pinning



# 8-bit dual supply translating transceiver; 3-state

# 5.2 Pin description

Table 2. Pin description

	<u> </u>	
Symbol	Pin	Description
$V_{CC(A)}$	1	supply voltage A (An, $\overline{\text{OE}}$ and DIR inputs are referenced to $V_{\text{CC(A)}}$ )
DIR	2	direction control
A1 to A8	3, 4, 5, 6, 7, 8, 9, 10	data input or output
GND[1]	11	ground (0 V)
GND[1]	12	ground (0 V)
GND[1]	13	ground (0 V)
B1 to B8	21, 20, 19, 18, 17, 16, 15, 14	data input or output
ŌĒ	22	output enable input (active LOW)
V <sub>CC(B)</sub>	23	supply voltage B (Bn inputs are referenced to V <sub>CC(B)</sub> )
V <sub>CC(B)</sub>	24	supply voltage B (Bn inputs are referenced to V <sub>CC(B)</sub> )

<sup>[1]</sup> All GND pins must be connected to ground (0 V).

# 6. Functional description

Table 3. Function table [1]

Supply voltage	Input		Input/output[3]	
V <sub>CC(A)</sub> , V <sub>CC(B)</sub>	OE[2]	DIR[2]	An[2]	Bn
0.8 V to 3.6 V	L	L	An = Bn	input
0.8 V to 3.6 V	L	Н	input	Bn = An
0.8 V to 3.6 V	Н	Χ	Z	Z
GND[3]	X	X	Z	Z

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		-0.5	+4.6	V
V <sub>CC(B)</sub>	supply voltage B		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
V <sub>I</sub>	input voltage		<u>[1]</u> –0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode	[1][2][3] -0.5	$V_{CCO} + 0.5$	V
		Suspend or 3-state mode	<u>[1]</u> –0.5	+4.6	V
I <sub>O</sub>	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I <sub>CC</sub>	supply current	$I_{CC(A)}$ or $I_{CC(B)}$	-	100	mA

74AVC8T245

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<sup>[2]</sup> The An, DIR and  $\overline{\text{OE}}$  input circuit is referenced to  $V_{\text{CC(A)}}$ ; The Bn input circuit is referenced to  $V_{\text{CC(B)}}$ .

<sup>[3]</sup> If at least one of  $V_{CC(A)}$  or  $V_{CC(B)}$  is at GND level, the device goes into suspend mode.

### 8-bit dual supply translating transceiver; 3-state

 Table 4.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$I_{GND}$	ground current		-100	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	<u>[4]</u> _	500	mW

- [1] The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.
- [2] V<sub>CCO</sub> is the supply voltage associated with the output port.
- [3]  $V_{CCO} + 0.5 \text{ V}$  should not exceed 4.6 V.
- [4] For TSSOP24 package:  $P_{tot}$  derates linearly at 5.5 mW/K above 60 °C. For DHVQFN24 package:  $P_{tot}$  derates linearly at 4.5 mW/K above 60 °C.

# 8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		8.0	3.6	V
$V_{CC(B)}$	supply voltage B		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	<u>[1]</u> 0	$V_{CCO}$	V
		Suspend or 3-state mode	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CCI} = 0.8 \text{ V to } 3.6 \text{ V}$	<u>[2]</u> _	5	ns/V

<sup>[1]</sup>  $V_{CCO}$  is the supply voltage associated with the output port.

# 9. Static characteristics

Table 6. Typical static characteristics at  $T_{amb} = 25 \, ^{\circ}C_{-}^{[1][2]}$ 

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = -1.5 \text{ mA}; \ V_{CC(A)} = V_{CC(B)} = 0.8 \ V$	-	0.69	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = 1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.07	-	V
I <sub>I</sub>	input leakage current	DIR, $\overline{OE}$ input; $V_I = 0 \text{ V or } 3.6 \text{ V}$ ; $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	±0.025	±0.25	μΑ
l <sub>OZ</sub>	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$ ; $V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$	[3] -	±0.5	±2.5	μΑ
		suspend mode A port; $V_O = 0 \text{ V or } V_{CCO}$ ; $V_{CC(A)} = 3.6 \text{ V}$ ; $V_{CC(B)} = 0 \text{ V}$	[3] _	±0.5	±2.5	μΑ
		suspend mode B port; $V_O = 0 \text{ V or } V_{CCO}$ ; $V_{CC(A)} = 0 \text{ V}$ ; $V_{CC(B)} = 3.6 \text{ V}$	[3] -	±0.5	±2.5	μΑ

V<sub>CCI</sub> is the supply voltage associated with the input port.

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Table 6. Typical static characteristics at  $T_{amb} = 25 \, {}^{\circ}C_{\underline{1}\underline{1}\underline{2}\underline{1}}$  ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>OFF</sub>	power-off leakage current	A port; $V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	±0.1	±1	μΑ
		B port; $V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	±0.1	±1	μΑ
Cı	input capacitance	DIR, $\overline{OE}$ input; $V_I = 0 \text{ V or } 3.3 \text{ V}$ ; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	1.5	-	pF
C <sub>I/O</sub>	input/output capacitance	A and B port; $V_O = 3.3 \text{ V or } 0 \text{ V}$ ; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	4.3	-	pF

<sup>[1]</sup>  $V_{CCO}$  is the supply voltage associated with the output port.

Table 7. Static characteristics [1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C t	o +85 °C	–40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
$V_{IH}$	HIGH-level	data input	'				
	input voltage	$V_{CCI} = 0.8 \text{ V}$	0.70V <sub>CCI</sub>	-	0.70V <sub>CCI</sub>	-	V
		V <sub>CCI</sub> = 1.1 V to 1.95 V	0.65V <sub>CCI</sub>	-	0.65V <sub>CCI</sub>	-	V
		V <sub>CCI</sub> = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		V <sub>CCI</sub> = 3.0 V to 3.6 V	2	-	2	-	V
		DIR, OE input					
		$V_{CC(A)} = 0.8 \text{ V}$	0.70V <sub>CC(A)</sub>	-	0.70V <sub>CC(A)</sub>	-	V
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	0.65V <sub>CC(A)</sub>	-	0.65V <sub>CC(A)</sub>	-	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	1.6	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V
V <sub>IL</sub>	LOW-level	data input					
	input voltage	V <sub>CCI</sub> = 0.8 V	-	$0.30V_{CCI}$	-	$0.30V_{CCI}$	V
		V <sub>CCI</sub> = 1.1 V to 1.95 V	-	$0.35V_{CCI}$	-	$0.35V_{CCI}$	V
		V <sub>CCI</sub> = 2.3 V to 2.7 V	-	0.7	-	0.7	V
		V <sub>CCI</sub> = 3.0 V to 3.6 V	-	0.8	-	0.8	V
		DIR, OE input					
		$V_{CC(A)} = 0.8 \text{ V}$	-	0.30V <sub>CC(A)</sub>	-	0.30V <sub>CC(A)</sub>	V
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	-	0.35V <sub>CC(A)</sub>	-	0.35V <sub>CC(A)</sub>	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	-	0.8	-	0.8	V

<sup>[2]</sup>  $V_{\text{CCI}}$  is the supply voltage associated with the data input port.

<sup>[3]</sup> For I/O ports, the parameter I<sub>OZ</sub> includes the input leakage current.

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**Table 7.** Static characteristics ...continued 11[2]
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to	+85 °C	–40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
$V_{OH}$	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$	'				
	output voltage	$I_O = -100 \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	V <sub>CCO</sub> - 0.1	-	V <sub>CCO</sub> - 0.1	-	V
		$I_O = -3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	0.85	-	V
		$I_O = -6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05	-	1.05	-	V
		$I_O = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	1.2	-	V
		$I_O = -9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	1.75	-	V
		$I_O = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	V
0_	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$					
		$I_O = 100 \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	0.1	-	0.1	V
		$I_O = 3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	-	0.25	-	0.25	V
		$I_O = 6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	0.35	-	0.35	V
		$I_O = 8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	-	0.45	-	0.45	V
		$I_O = 9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	-	0.55	-	0.55	V
		$I_O = 12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	-	0.7	-	0.7	V
l <sub>l</sub>	input leakage current	DIR, $\overline{OE}$ input; $V_1 = 0 \text{ V or } 3.6 \text{ V};$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	±1	-	±5	μА
l <sub>OZ</sub>	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$ ; $V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$	[3]	±5	-	±30	μА
		suspend mode A port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 3.6 \text{ V};$ $V_{CC(B)} = 0 \text{ V}$	[3] -	±5	-	±30	μΑ
		suspend mode B port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 0 \text{ V};$ $V_{CC(B)} = 3.6 \text{ V}$	[3]	±5	-	±30	μΑ
I <sub>OFF</sub>	power-off leakage	A port; $V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	±5	-	±30	μΑ
	current	B port; $V_1$ or $V_O = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	±5	-	±30	μΑ

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**Table 7.** Static characteristics ...continued[1][2]
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C t	o +85 °C	–40 °C to	-40 °C to +125 °C	
			Min	Max	Min	Max	
$I_{CC}$	supply current	A port; $V_I = 0 \text{ V or } V_{CCI}$ ; $I_O = 0 \text{ A}$	'				'
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	10	-	55	μΑ
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	8	-	50	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	8	-	50	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-2	-	-12	-	μΑ
		B port; $V_I = 0 \text{ V or } V_{CCI}$ ; $I_O = 0 \text{ A}$					
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	10	-	55	μΑ
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	8	-	50	μА
		V <sub>CC(A)</sub> = 3.6 V; V <sub>CC(B)</sub> = 0 V	-2	-	-12	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-	8	-	50	μΑ
		A plus B port ( $I_{CC(A)} + I_{CC(B)}$ ); $I_O = 0$ A; $V_I = 0$ V or $V_{CCI}$ ; $V_{CC(A)} = 0.8$ V to 3.6 V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	20	-	70	μА
		A plus B port ( $I_{CC(A)} + I_{CC(B)}$ ); $I_O = 0$ A; $V_I = 0$ V or $V_{CCI}$ ; $V_{CC(A)} = 1.1$ V to 3.6 V; $V_{CC(B)} = 1.1$ V to 3.6 V	-	16	-	65	μА

<sup>[1]</sup>  $V_{CCO}$  is the supply voltage associated with the output port.

Table 8. Typical total supply current  $(I_{CC(A)} + I_{CC(B)})$ 

V <sub>CC(A)</sub>	V <sub>CC(B)</sub>	V <sub>CC(B)</sub>					Unit	
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μΑ
0.8 V	0.1	0.1	0.1	0.1	0.1	0.3	1.6	μΑ
1.2 V	0.1	0.1	0.1	0.1	0.1	0.1	0.8	μΑ
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.4	μΑ
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.2	μΑ
2.5 V	0.1	0.3	0.1	0.1	0.1	0.1	0.1	μΑ
3.3 V	0.1	1.6	0.8	0.4	0.2	0.1	0.1	μΑ

<sup>[2]</sup> V<sub>CCI</sub> is the supply voltage associated with the data input port.

<sup>[3]</sup> For I/O ports, the parameter  $I_{\text{OZ}}$  includes the input leakage current.

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# 10. Dynamic characteristics

Table 9. Typical dynamic characteristics at  $V_{CC(A)} = 0.8 \text{ V}$  and  $T_{amb} = 25 ^{\circ}\text{C}$  [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

Symbol	Parameter	Conditions	V <sub>CC(B)</sub>							
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V		
$t_{pd}$	propagation delay	An to Bn	14.4	7.0	6.2	6.0	5.9	6.0	ns	
		Bn to An	14.4	12.4	12.1	11.9	11.8	11.8	ns	
t <sub>dis</sub>	disable time	OE to An	16.2	16.2	16.2	16.2	16.2	16.2	ns	
		OE to Bn	17.6	10.0	9.0	9.1	8.7	9.3	ns	
t <sub>en</sub>	enable time	OE to An	21.9	21.9	21.9	21.9	21.9	21.9	ns	
		OE to Bn	22.2	11.1	9.8	9.4	9.4	9.6	ns	

<sup>[1]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

Table 10. Typical dynamic characteristics at  $V_{CC(B)} = 0.8 \text{ V}$  and  $T_{amb} = 25 \,^{\circ}\text{C}$  [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

•									-
Symbol	Parameter	Conditions	V <sub>CC(A)</sub>						
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t <sub>pd</sub>	propagation delay	An to Bn	14.4	12.4	12.1	11.9	11.8	11.8	ns
		Bn to An	14.4	7.0	6.2	6.0	5.9	6.0	ns
t <sub>dis</sub>	disable time	OE to An	16.2	5.9	4.4	4.2	3.1	3.5	ns
		OE to Bn	17.6	14.2	13.7	13.6	13.3	13.1	ns
t <sub>en</sub>	enable time	OE to An	21.9	6.4	4.4	3.5	2.6	2.3	ns
		OE to Bn	22.2	17.7	17.2	17.0	16.8	16.7	ns

<sup>[1]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

## 8-bit dual supply translating transceiver; 3-state

Table 11. Typical power dissipation capacitance at  $V_{CC(A)} = V_{CC(B)}$  and  $T_{amb} = 25 \, ^{\circ}C$  [1][2] Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			V <sub>CC(A)</sub> =	V <sub>CC(B)</sub>			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C <sub>PD</sub> power dissipation capacitance		A port: (direction An to Bn); output enabled	0.2	0.2	0.2	0.3	0.4	0.5	pF
	A port: (direction An to Bn); output disabled	0.2	0.2	0.2	0.3	0.4	0.5	pF	
		A port: (direction Bn to An); output enabled	9	9	10	10	11	13	pF
		A port: (direction Bn to An); output disabled	0.6	0.6	0.6	0.7	0.7	8.0	pF
		B port: (direction An to Bn); output enabled	9	9	10	10	11	13	pF
		B port: (direction An to Bn); output disabled	0.6	0.6	0.6	0.7	0.7	8.0	pF
		B port: (direction Bn to An); output enabled	0.2	0.2	0.2	0.3	0.4	0.5	pF
		B port: (direction Bn to An); output disabled	0.2	0.2	0.2	0.3	0.4	0.5	pF

<sup>[1]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

C<sub>L</sub> = load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

[2]  $f_i$  = 10 MHz;  $V_I$  = GND to  $V_{CC}$ ;  $t_r$  =  $t_f$  = 1 ns;  $C_L$  = 0 pF;  $R_L$  =  $\infty$   $\Omega$ .

## 8-bit dual supply translating transceiver; 3-state

Table 12. Dynamic characteristics for temperature range -40 °C to +85 °C [1] Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions					_	C(B)					Unit
			1.2 V	± 0.1 V	1.5 V	± 0.1 V	1.8 V ±	± 0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V <sub>CC(A)</sub> =	1.1 V to 1.3 V												
t <sub>pd</sub>	propagation	An to Bn	0.5	9.0	0.5	6.7	0.5	5.8	0.5	4.9	0.5	4.8	ns
	delay	Bn to An	0.5	9.0	0.5	8.5	0.5	8.3	0.5	8.0	0.5	7.8	ns
t <sub>dis</sub>	disable time	OE to An	0.5	11.8	0.5	11.8	0.5	11.8	0.5	11.8	0.5	11.8	ns
		OE to Bn	0.5	12.3	0.5	9.5	0.5	9.4	0.5	8.0	0.5	8.9	ns
t <sub>en</sub>	enable time	OE to An	1.1	14.4	1.1	14.4	1.1	14.4	1.1	14.4	1.1	14.4	ns
		OE to Bn	1.1	14.2	1.1	10.4	1.1	9.0	1.0	7.7	1.0	7.3	ns
V <sub>CC(A)</sub> =	1.4 V to 1.6 V												
t <sub>pd</sub>	propagation	An to Bn	0.5	8.5	0.5	5.6	0.5	4.7	0.5	4.4	0.5	4.1	ns
	delay	Bn to An	0.5	6.7	0.5	5.6	0.5	5.3	0.5	5.2	0.5	5.0	ns
t <sub>dis</sub>	disable time	OE to An	0.5	8.6	0.5	8.6	0.5	8.6	0.5	8.6	0.5	8.6	ns
		OE to Bn	0.5	11.2	0.5	8.4	0.5	7.6	0.5	7.2	0.5	7.8	ns
t <sub>en</sub>	enable time	OE to An	1.1	8.7	1.1	8.7	1.1	8.7	1.1	8.7	1.1	8.7	ns
		OE to Bn	1.1	12.8	1.1	8.1	1.1	7.1	1.0	5.6	1.0	5.2	ns
V <sub>CC(A)</sub> =	1.65 V to 1.95	V											
t <sub>pd</sub> propagation delay	propagation	An to Bn	0.5	8.3	0.5	5.3	0.5	4.5	0.5	3.8	0.5	3.5	ns
	delay	Bn to An	0.5	5.8	0.5	4.7	0.5	4.5	0.5	4.3	0.5	4.1	ns
t <sub>dis</sub>	disable time	OE to An	0.5	7.1	0.5	7.1	0.5	7.1	0.5	7.1	0.5	7.1	ns
		OE to Bn	0.5	10.9	0.5	7.8	0.5	6.9	0.5	6.0	0.5	5.8	ns
t <sub>en</sub>	enable time	OE to An	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	ns
		OE to Bn	1.1	12.4	1.1	8.2	1.0	6.7	0.5	5.1	0.5	4.5	ns
$V_{CC(A)} =$	2.3 V to 2.7 V												
t <sub>pd</sub>	propagation	An to Bn	0.5	8.0	0.5	5.2	0.5	4.3	0.5	3.3	0.5	2.9	ns
	delay	Bn to An	0.5	4.9	0.5	4.4	0.5	3.8	0.5	3.3	0.5	3.1	ns
t <sub>dis</sub>	disable time	OE to An	0.5	5.1	0.5	5.1	0.5	5.1	0.5	5.1	0.5	5.1	ns
		OE to Bn	0.5	10.4	0.5	7.1	0.5	6.3	0.5	5.1	0.5	5.2	ns
t <sub>en</sub>	enable time	OE to An	0.5	4.8	0.5	4.8	0.5	4.8	0.5	4.8	0.5	4.8	ns
		OE to Bn	1.1	11.9	1.1	7.9	0.5	6.4	0.5	4.6	0.5	4.0	ns
V <sub>CC(A)</sub> =	3.0 V to 3.6 V												
t <sub>pd</sub>	propagation	An to Bn	0.5	7.8	0.5	5.0	0.5	4.1	0.5	3.1	0.5	2.7	ns
	delay	Bn to An	0.5	4.8	0.5	4.1	0.5	3.5	0.5	2.9	0.5	2.7	ns
t <sub>dis</sub>	disable time	OE to An	0.5	4.9	0.5	4.9	0.5	4.9	0.5	4.9	0.5	4.9	ns
		OE to Bn	0.5	10.1	0.5	6.9	0.5	6.0	0.5	4.8	0.5	5.0	ns
t <sub>en</sub>	enable time	OE to An	0.5	4.0	0.5	4.0	0.5	4.0	0.5	4.0	0.5	4.0	ns
		OE to Bn	1.1	11.7	1.1	7.8	0.5	6.2	0.5	4.5	0.5	3.9	ns

<sup>[1]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

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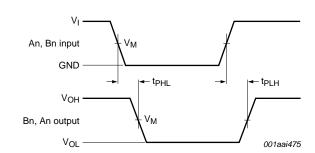
Table 13. Dynamic characteristics for temperature range –40 °C to +125 °C 1 Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

Symbol	Parameter	Conditions					V <sub>C</sub>	C(B)					Unit
			1.2 V	± 0.1 V	1.5 V	± 0.1 V	1.8 V ±	0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V <sub>CC(A)</sub> =	1.1 V to 1.3 V		'		•			'			•	'	
t <sub>pd</sub>	propagation	An to Bn	0.5	9.9	0.5	7.4	0.5	6.4	0.5	5.4	0.5	5.3	ns
	delay	Bn to An	0.5	9.9	0.5	9.4	0.5	9.2	0.5	8.8	0.5	8.6	ns
t <sub>dis</sub>	disable time	OE to An	0.5	13.0	0.5	13.0	0.5	13.0	0.5	13.0	0.5	13.0	ns
		OE to Bn	0.5	13.6	0.5	10.5	0.5	10.4	0.5	8.8	0.5	9.8	ns
t <sub>en</sub>	enable time	OE to An	1.1	15.9	1.1	15.9	1.1	15.9	1.1	15.9	1.1	15.9	ns
		OE to Bn	1.1	15.7	1.1	11.5	1.1	9.9	1.0	8.5	1.0	8.1	ns
V <sub>CC(A)</sub> =	1.4 V to 1.6 V												
t <sub>pd</sub>	propagation	An to Bn	0.5	9.4	0.5	6.2	0.5	5.2	0.5	4.9	0.5	4.6	ns
	delay	Bn to An	0.5	7.4	0.5	6.2	0.5	5.9	0.5	5.8	0.5	5.5	ns
t <sub>dis</sub>	disable time	OE to An	0.5	9.5	0.5	9.5	0.5	9.5	0.5	9.5	0.5	9.5	ns
		OE to Bn	0.5	12.4	0.5	9.3	0.5	8.4	0.5	8.0	0.5	8.6	ns
t <sub>en</sub>	enable time	OE to An	1.1	9.6	1.1	9.6	1.1	9.6	1.1	9.6	1.1	9.6	ns
		OE to Bn	1.1	14.1	1.1	9.0	1.1	7.9	1.0	6.2	1.0	5.8	ns
V <sub>CC(A)</sub> =	1.65 V to 1.95	V											
t <sub>pd</sub> propagation	An to Bn	0.5	9.2	0.5	5.9	0.5	5.0	0.5	4.2	0.5	3.9	ns	
	delay	Bn to An	0.5	6.4	0.5	5.2	0.5	5.0	0.5	4.8	0.5	4.6	ns
t <sub>dis</sub>	disable time	OE to An	0.5	7.9	0.5	7.9	0.5	7.9	0.5	7.9	0.5	7.9	ns
		OE to Bn	0.5	12.0	0.5	8.6	0.5	7.6	0.5	6.6	0.5	6.4	ns
t <sub>en</sub>	enable time	OE to An	1.0	7.5	1.0	7.5	1.0	7.5	1.0	7.5	1.0	7.5	ns
		OE to Bn	1.1	13.7	1.1	9.1	1.0	7.4	0.5	5.7	0.5	5.0	ns
$V_{CC(A)} =$	2.3 V to 2.7 V												
$t_{pd}$	propagation	An to Bn	0.5	8.8	0.5	5.8	0.5	4.8	0.5	3.7	0.5	3.2	ns
	delay	Bn to An	0.5	5.4	0.5	4.9	0.5	4.2	0.5	3.7	0.5	3.5	ns
t <sub>dis</sub>	disable time	OE to An	0.5	5.7	0.5	5.7	0.5	5.7	0.5	5.7	0.5	5.7	ns
		OE to Bn	0.5	11.5	0.5	7.9	0.5	7.0	0.5	5.7	0.5	5.8	ns
t <sub>en</sub>	enable time	OE to An	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	ns
		OE to Bn	1.1	13.1	1.1	8.7	0.5	7.1	0.5	5.1	0.5	4.4	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t <sub>pd</sub>	propagation	An to Bn	0.5	8.6	0.5	5.5	0.5	4.6	0.5	3.5	0.5	3.0	ns
	delay	Bn to An	0.5	5.3	0.5	4.6	0.5	3.9	0.5	3.2	0.5	3.0	ns
t <sub>dis</sub>	disable time	OE to An	0.5	5.4	0.5	5.4	0.5	5.4	0.5	5.4	0.5	5.4	ns
		OE to Bn	0.5	11.2	0.5	7.6	0.5	6.6	0.5	5.3	0.5	5.5	ns
t <sub>en</sub>	enable time	OE to An	0.5	4.4	0.5	4.4	0.5	4.4	0.5	4.4	0.5	4.4	ns
		OE to Bn	1.1	12.9	1.1	8.6	0.5	6.9	0.5	5.0	0.5	4.3	ns

<sup>[1]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ ;  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ ;  $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

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# 11. Waveforms



Measurement points are given in Table 14.

V<sub>OL</sub> and V<sub>OH</sub> are typical output voltage levels that occur with the output load.

Fig 5. The data input (An, Bn) to output (Bn, An) propagation delay times

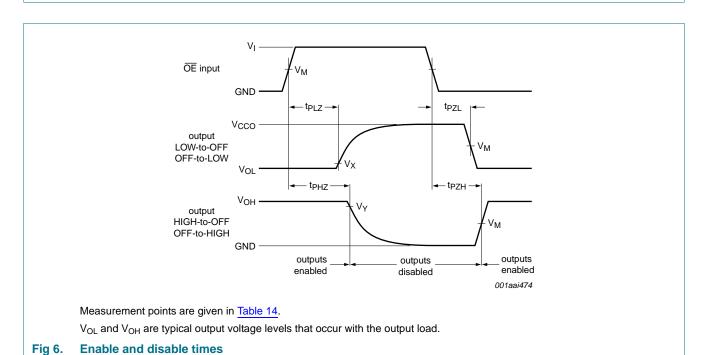
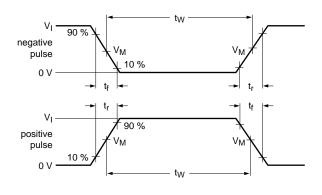


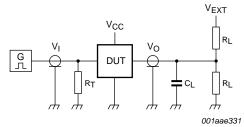
Table 14. Measurement points

Supply voltage	Input <sup>[1]</sup>	Output <sup>[2]</sup>						
V <sub>CC(A)</sub> , V <sub>CC(B)</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>				
0.8 V to 1.6 V	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.1 V	$V_{OH}-0.1\ V$				
1.65 V to 2.7 V	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.15 V	V <sub>OH</sub> – 0.15 V				
3.0 V to 3.6 V	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> – 0.3 V				

- [1]  $V_{CCI}$  is the supply voltage associated with the data input port.
- [2] V<sub>CCO</sub> is the supply voltage associated with the output port.

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Test data is given in Table 15.

R<sub>L</sub> = Load resistance.

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance.

 $V_{\mathsf{EXT}}$  = External voltage for measuring switching times.

Fig 7. Load circuit for switching times

Table 15. Test data

Supply voltage	Input		Load		V <sub>EXT</sub>		
V <sub>CC(A)</sub> , V <sub>CC(B)</sub>	V <sub>I</sub> [1]	∆ <b>t/</b> ∆V[2]	C <sub>L</sub>	R <sub>L</sub>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub> [3]
0.8 V to 1.6 V	V <sub>CCI</sub>	≤1.0 ns/V	15 pF	2 kΩ	open	GND	2V <sub>CCO</sub>
1.65 V to 2.7 V	V <sub>CCI</sub>	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V <sub>CCO</sub>
3.0 V to 3.6 V	V <sub>CCI</sub>	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V <sub>CCO</sub>

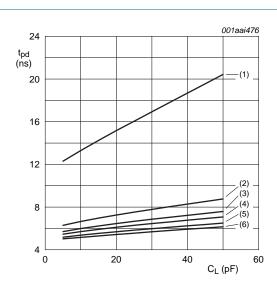
[1]  $V_{CCI}$  is the supply voltage associated with the data input port.

[2]  $dV/dt \ge 1.0 V/ns$ 

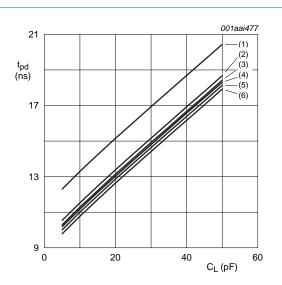
[3]  $V_{CCO}$  is the supply voltage associated with the output port.

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# 12. Typical propagation delay characteristics

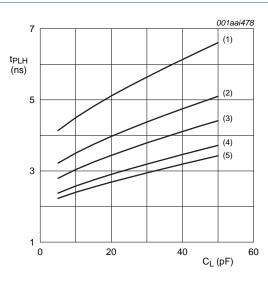


- a. Propagation delay (An to Bn);  $V_{CC(A)} = 0.8 \text{ V}$
- (1)  $V_{CC(B)} = 0.8 \text{ V}.$
- (2)  $V_{CC(B)} = 1.2 \text{ V}.$
- (3)  $V_{CC(B)} = 1.5 \text{ V}.$
- (4)  $V_{CC(B)} = 1.8 \text{ V}.$
- (5)  $V_{CC(B)} = 2.5 \text{ V}.$
- (6)  $V_{CC(B)} = 3.3 \text{ V}.$

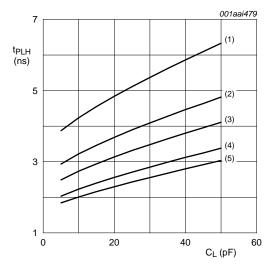


- b. Propagation delay (An to Bn);  $V_{CC(B)} = 0.8 \text{ V}$
- (1)  $V_{CC(A)} = 0.8 \text{ V}.$
- (2)  $V_{CC(A)} = 1.2 \text{ V}.$
- (3)  $V_{CC(A)} = 1.5 \text{ V}.$
- (4)  $V_{CC(A)} = 1.8 \text{ V}.$ (5)  $V_{CC(A)} = 2.5 \text{ V}.$
- (6)  $V_{CC(A)} = 3.3 \text{ V}.$
- Fig 8. Typical propagation delay versus load capacitance; T<sub>amb</sub> = 25 °C

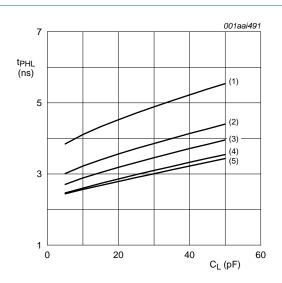
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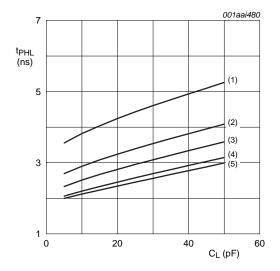
a. LOW to HIGH propagation delay (An to Bn);  $V_{CC(A)} = 1.2 \text{ V}$ 



- c. LOW to HIGH propagation delay (An to Bn);  $V_{CC(A)} = 1.5 \text{ V}$
- (1)  $V_{CC(B)} = 1.2 \text{ V}.$
- (2)  $V_{CC(B)} = 1.5 \text{ V}.$
- (3)  $V_{CC(B)} = 1.8 \text{ V}.$
- (4)  $V_{CC(B)} = 2.5 \text{ V}.$
- (5)  $V_{CC(B)} = 3.3 \text{ V}.$



b. HIGH to LOW propagation delay (An to Bn);  $V_{CC(A)} = 1.2 \text{ V}$ 



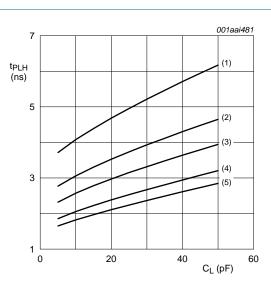
d. HIGH to LOW propagation delay (An to Bn);  $V_{CC(A)} = 1.5 \text{ V}$ 

Fig 9. Typical propagation delay versus load capacitance; T<sub>amb</sub> = 25 °C

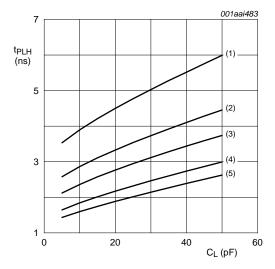
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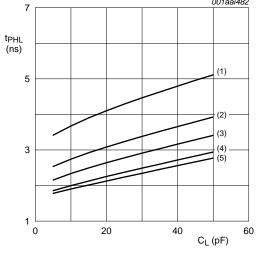
a. LOW to HIGH propagation delay (An to Bn);  $V_{CC(A)} = 1.8 \text{ V}$ 



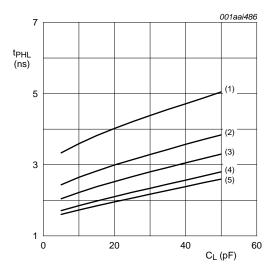
c. LOW to HIGH propagation delay (An to Bn);  $V_{CC(A)} = 2.5 \text{ V}$ 



- (2)  $V_{CC(B)} = 1.5 \text{ V}.$
- (3)  $V_{CC(B)} = 1.8 \text{ V}.$
- (4)  $V_{CC(B)} = 2.5 \text{ V}.$
- (5)  $V_{CC(B)} = 3.3 \text{ V}.$



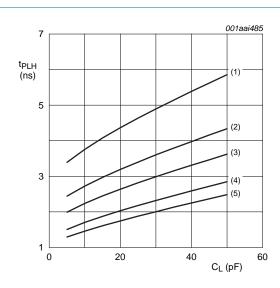
b. HIGH to LOW propagation delay (An to Bn);  $V_{CC(A)} = 1.8 \text{ V}$ 

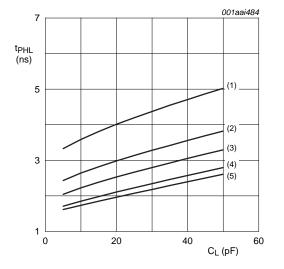


d. HIGH to LOW propagation delay (An to Bn);  $V_{CC(A)} = 2.5 \text{ V}$ 

Fig 10. Typical propagation delay versus load capacitance; T<sub>amb</sub> = 25 °C

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- a. LOW to HIGH propagation delay (An to Bn);  $V_{CC(A)} = 3.3 \text{ V}$
- (1)  $V_{CC(B)} = 1.2 \text{ V}.$
- (2)  $V_{CC(B)} = 1.5 \text{ V}.$
- (3)  $V_{CC(B)} = 1.8 \text{ V}.$
- (4)  $V_{CC(B)} = 2.5 \text{ V}.$
- (5)  $V_{CC(B)} = 3.3 \text{ V}.$

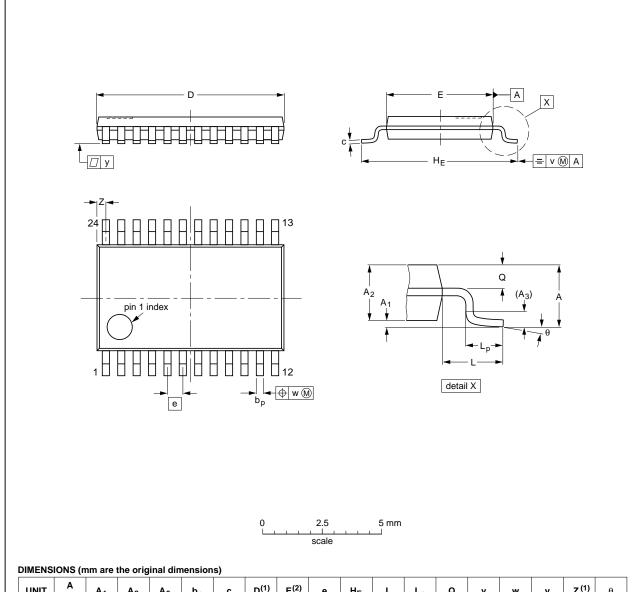
b. HIGH to LOW propagation delay (An to Bn);  $V_{\text{CC(A)}} = 3.3 \text{ V}$ 

Fig 11. Typical propagation delay versus load capacitance;  $T_{amb}$  = 25  $^{\circ}$ C

# 13. Package outline

TSSOP24: plastic thin shrink small outline package; 24 leads; body width 4.4 mm

SOT355-1



						-,												
UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	7.9 7.7	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT355-1		MO-153			<del>99-12-27</del> 03-02-19	

Fig 12. Package outline SOT355-1 (TSSOP24)

74AVC8T245

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# DHVQFN24: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body $3.5 \times 5.5 \times 0.85$ mm

SOT815-1

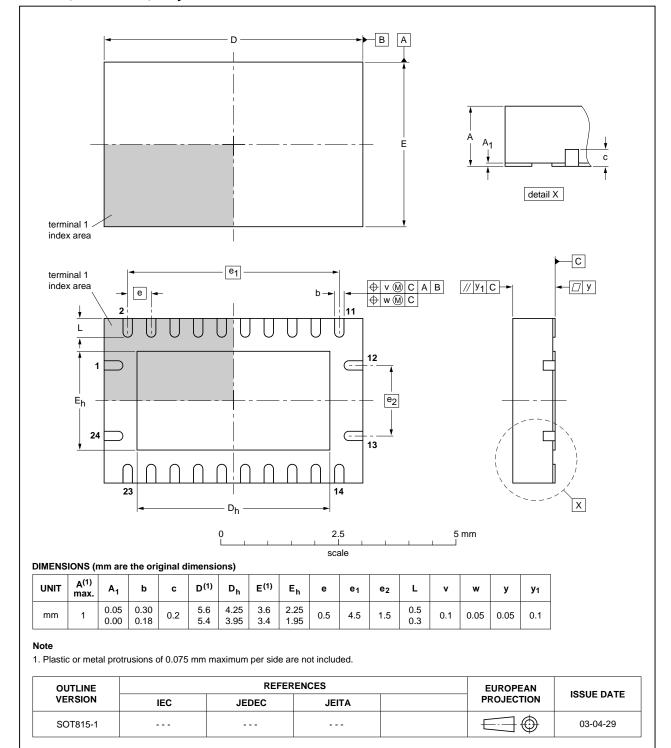


Fig 13. Package outline SOT815-1 (DHVQFN24)

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# 14. Abbreviations

### Table 16. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

# 15. Revision history

## Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVC8T245 v.3	20110928	Product data sheet	-	74AVC8T245 v.2
Modifications:	General dea	scription corrected (errata).		
74AVC8T245 v.2	20090428	Product data sheet	-	74AVC8T245 v.1
Modifications:	Section 5 "I	Pinning information":		
	Changed: p	in names changed in pin de	escription table.	
74AVC8T245 v.1	20080711	Product data sheet	-	-

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# 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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